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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
K.N.	AC		Abstract of: Oxidation of Sintered Aluminum Nitride at Near-ambient temperatures; Dutta, I.; Mitra, S. ; Rabenberg, L.; Journal of the American Ceramic Society, Vol. 75, No. 11, pp. 3149-53, Nov. 1992				
	AD		Abstract of: Oxidation of lead films by rf sputter etching in an oxygen plasma; J.H. Greiner				
	AE		Abstract of: Josephson Tunneling Barriers by rf Sputter Etching in an Oxygen Plasma; J.H. Greiner; Journal of Applied Physics; Vol. 42; Number 12; November 1971				
	AF		Abstract of: Measurement of Tunnel Current Density in a Metal Oxide Metal System as a Function of Oxide Thickness; J.M. Eldridge and J. Matisoo				
	AG		Abstract of: Optical Measurement of Film Growth on Silicon and Germanium Surfaces in Room Air; R.J. Archer				
	AH		Preparation of Al-O-N Films by Electron Cyclotron Resonance Plasma-Assisted Chemical Vapor Deposition; Takashi Goto; Wei Zhang; Toshio Hirai, 1999 Publication Board, Japanese Journal of Applied Physics; Vol. 38 (1999) Pt. 1, No. 6A; pp. 3668-74				
	AI		Ion assisted deposition of oxynitrides of aluminum and silicon; G.A. Al-Jumaily and T.A. Mooney; W.A. Spurgeon and H.M. Dauplaise				
K.N.	AJ		Abstract of: Preparation of aluminum nitride and oxynitride thin films by ion-assisted deposition; Targove, J.D.; Lingg, L.J.; Lehan, J.P. et al.; Conference: Materials Modification and Growth Using Ion Beams Symposium, pp. 311-16; Mater. Res. Soc., Pittsburgh, PA 1987				
EXAMINER				DATE CONSIDERED			
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K.N.	AC		Film Synthesis and Growth Using Energetic Beams; Material Research Society Symposium Proceedings Vol. 388; April 17-20, 1995 San Francisco, CA			
	AD		Some Properties of Chemically Vapor Deposited Films of $Al_2O_3N_x$ on Silicon; E.A. Irene, V.J. Silvestri and G.R. Woolhouse; Journal of Electronic Materials, Vol. 4, No. 3, 1975; pp. 409-427			
	AE		Chemical Vapor Deposition of $Al_2O_3N_x$ Films; V.J. Silvestri, E.A. Irene, S. Zirinsky; J.D. Kuptsis; Journal of Electronic Materials, Vol. 4, No. 3, 1975; pp. 429-444			
	AF		Disk hydrogen plasma assisted chemical vapor deposition of aluminum nitride; T.Y. Sheng, Z.Q. Yu, and G.J. Collins; Appl. Phys. Lett. 52(7), February 1988; pp. 576-578			
	AG		Epitaxial Growth of Aluminum Nitride on Sapphire and Silicon; K. Dovidenko; S. Oktyabrsky; J. Narayan; and M. Razeghi; Mat. Res. Soc. Symp. Proc. Vol. 358; 1995 Materials Research Society; pp. 1023-1028			
	AH		III-Nitride, SiC and Diamond Materials for Electronic Devices; Materials Research Society, Symposium Proceedings Vol. 423; April 8-12, 1996, San Francisco, CA; pp. 667-672			
	AI		Electrochemical Behaviour of AlN Films Prepared by Reactive Cathodic Sputtering; F. Vacandio, Y. Massiani, P. Gravier, L. Fedrizzi and D. Brida; Materials Science Forum; Vols. 289-292 (1998) pp. 689-697; 1998 Trans Tech Publications, Switzerland			
K.N.	AJ		Measurement of stress distribution in Si_3N_4 using AlN thin films; M. Akiyama, C.N. Xu, K. Nonaka, T. Watanabe; Journal of Materials Science Letters (1998) pp. 2093-2095			
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K. Khemnguyen			08/16/02			
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K.N.	AD		Changes in optical transmittance and surface morphology of AlN thin films exposed to atmosphere; Yoshihisa Watanabe, Yoshifumi Sakuragi, Yoshiki Amamoto, and Yoshikazu Nakamura; J. Mater. Res., Vol 13, No. 10, Oct. 1998; 1998 Materials Research Society; pp. 2956-61				
	AE		Optical Interference Coatings; Florin Abeles, Chair/Editor; Proceedings Europto Series; SPIE Vol. 2253; part 2 of 2; pp. 1275-85				
	AF		Tunneling Leakage Current in Ultrathin (<4nm) Nitride/Oxide Stack Dielectrics; Ying Shi; Xiewen Wang; T.P. Ma; IEEE Electron Device Letters, Vol. 19, No. 10, October 1998; pp. 388-390				
	AG		High Quality Ultra-thin (1.5 nm) TiO ₂ /Si ₃ N ₄ Gate Dielectric for Deep Sub-micron CMOS Technology; Xin Guo, Xiewen Wang; Sijiong Luo, T.P. Ma, and T. Tamagawa; Dept. of Electrical Engineering, Yale University, New Haven, CT 06520				
	AH		High Quality Ta ₂ O ₅ Gate Dielectrics with T _{ox,eq} < 10Å; H. F. Luan, S.J. Lee, C.H. Lee, S.C. Song, Y.L. Mao, Y. Senzaki, D. Roberts and D.L. Kwong				
	AI		Abstract of: Low interface trap density for remote plasma deposited SiO ₂ /sub 2/ on n-type GaN; Applied Physics Letters, Vol. 68, No. 13; pp. 1850-2				
K.N.	AJ		Abstract of: Interface-state characteristics of GaN/GaAs MIS capacitors; Solid-State Electronics, vol. 25, no. 8, pp. 811-15				
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K.N.	AC		Applications of Aluminium Nitride Films Deposited by Reactive Sputtering to Silicon-on-Insulator Materials; Stefan Bengtsson, Mats Bergh, Manolis Choumas, Christian Olesen and Kjell O. Jeppson; Jpn. J. Appl. Phys. Vol. 35 (1996) Pt. 1, No. 8; pp. 4175-81				
	AD		Characteristics of AlN Thin Films Deposited by Electron Cyclotron Resonance Dual-Ion-Beam Sputtering and their Application to GHz-Bank Surface Acoustic Wave Devices; Hiroshi Okano, Naoki Tanaka, Yasuhiro Hirao, Yasumi Kobayashi, Kenichi Shibata and Shoichi Nakano; Jpn. J. Appl. Phys. Vol. 33 (1994); Pt. 1, No. 5B; pp. 2957-2961				
	AE		An Aluminum Oxynitride Film; Wang Dehuang, Guo Liang; Thin Solid Films, 198 (1991) pp. 207-210				
	AF		Formation of aluminum oxynitride diffusion barriers for Ag metallization; Y. Wang and T. L. Alford; Applied Physics Letters; Vol. 74, No. 1; 4 January 1999; American Institute of Physics; pp. 52-54				
	AG		Abstract of: Simulation of Hyperthermal deposition of Si and C on SiC surfaces; Applied Physics Letters; Vol. 74, No. 1; 4 January 1999; 1999 American Institute of Physics				
	AH		Nitrogen plasma source ion implantation for corrosion protection of aluminum 6061-T4; J. H. Booske, L. Zhang, W. Wang, K. Mente, N. Zjaba, C. Baum, and J.L. Shohet; J. Mater. Res. Vol. 12, No. 5, May 1997; 1997 Materials Research Society; pp. 1356-66				
	AI		Thickness measurement of submonolayer native oxide films on silicon wafers; Fuhe Li, Marjorie K. Balazs, Bruce E. Deal; Wafers & Substrates; Solid State Technology, February 2000; pp. 87, 88, 92, 94, 96, 98				
K.N.	AJ		Electrical Conduction and Dielectric Breakdown in Aluminum Oxide Insulators on Silicon; James Kolodzey et al.; IEEE Transactions on Electron Devices; Vol. 47, No. 1, January 2000; pp. 121-128				
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K.N.	AC		Structural, Optical and Electronic Properties of Oxidized AlN Thin Films at Different Temperatures; Enam Ahmed Chowdhury et al.;			
	AD		Formation of Al-nitride films at room temperature by nitrogen ion implantation into aluminum; N. Lieske and R. Hezel; J. Appl. Phys. 52(9), Sept. 1981; pp. 5806-5810			
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K.N.	AJ					
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